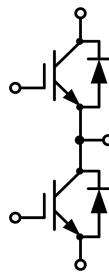


34mm Half Bridge IGBT Module

电气特性:

- 1200V 沟槽栅/场终止工艺
- 低开关损耗
- 正温度系数



典型应用:

- 逆变焊机
- 感应加热
- 高频开关应用
- 逆变器

$V_{CES}=1200V$, $I_{C\text{ nom}}=100A$ / $I_{CRM}=200A$

IGBT, 逆变器 / IGBT, Inverter

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value		Unit
集电极-发射极电压 Collector-Emitter voltage	$T_{vj}=25^\circ C$	V_{CES}	1200		V
连续集电极直流电流 Continuous DC collector current	$T_c=100^\circ C$, $T_{vj\text{ max}}=175^\circ C$	$I_{C\text{ nom}}$	100		A
集电极重复峰值电流 Repetitive peak collector current	$t_p=1 \text{ ms}$	I_{CRM}	200		A
栅极-发射极电压 Gate emitter voltage		V_{GE}	± 20		V

特征值 / Characteristic Values

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
集电极-发射极饱和电压 Collector-Emitter saturation voltage	$V_{GE}=15V$, $I_c=100A$	V_{CEsat}		1.98	2.50	V
	$V_{GE}=15V$, $I_c=100A$			2.25		
	$V_{GE}=15V$, $I_c=100A$			2.32		
栅极-发射极阈值电压 Gate-Emitter threshold voltage	$I_c = 3.8mA$, $V_{GE}=V_{CE}$	$V_{GE(th)}$	4.80	5.80	6.40	
栅电荷 Gate charge	$V_{GE}=-15V \dots +15V$	Q_G		0.49		μC

内部栅极电阻 Internal gate resistor	$T_{vj}=25^{\circ}\text{C}$	R_{Gint}		8.24		Ω
输入电容 Input capacitance	$f=1\text{MHz}, V_{CE}=25\text{ V}, V_{GE}=0\text{ V}$ $T_{vj}=25^{\circ}\text{C}$	C_{ies}		5.80		nF
反向传输电容 Reverse transfer capacitance		C_{res}		0.25		
集电极-发射极截止电流 Collector-emitter cut-off current	$V_{CE}=1200\text{V}, V_{GE}=0\text{ V}$ $T_{vj}=25^{\circ}\text{C}$	I_{CES}			1	mA
栅极-发射极漏电流 Gate-emitter leakage current	$V_{CE}=0\text{ V}, V_{GE}=20\text{ V}$ $T_{vj}=25^{\circ}\text{C}$	I_{GES}			100	nA
开通延迟时间 Turn-on delay time	$I_c=100\text{A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}, R_G=6.8\Omega$ (电感负载) / (inductive load) $T_{vj}=25^{\circ}\text{C}$ $T_{vj}=125^{\circ}\text{C}$ $T_{vj}=150^{\circ}\text{C}$	$t_{d\ on}$		182 191 207		ns
上升时间 Rise time	$I_c=100\text{A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}, R_G=6.8\Omega$ (电感负载) / (inductive load) $T_{vj}=25^{\circ}\text{C}$ $T_{vj}=125^{\circ}\text{C}$ $T_{vj}=150^{\circ}\text{C}$	t_r		41 43 40		
关断延迟时间 Turn-off delay time	$I_c=100\text{A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}, R_G=6.8\Omega$ (电感负载) / (inductive load) $T_{vj}=25^{\circ}\text{C}$ $T_{vj}=125^{\circ}\text{C}$ $T_{vj}=150^{\circ}\text{C}$	$t_{d\ off}$		254 308 326		
下降时间 Fall time	$I_c=100\text{A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}, R_G=6.8\Omega$ (电感负载) / (inductive load) $T_{vj}=25^{\circ}\text{C}$ $T_{vj}=125^{\circ}\text{C}$ $T_{vj}=150^{\circ}\text{C}$	t_f		61 102 114		
开通损耗能量 (每脉冲) Turn-on energy loss per pulse	$I_c=100\text{A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}, R_G=6.8\Omega$ $di/dt=1900\text{A}/\mu\text{s}$ ($T_{vj}=150^{\circ}\text{C}$) (电感负载) / (inductive load)	E_{on}		5.05 8.22 9.19		mJ
关断损耗能量 (每脉冲) Turn-off energy loss per pulse	$I_c=100\text{A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}, R_G=6.8\Omega$ $dv/dt=5600\text{V}/\mu\text{s}$ ($T_{vj}=150^{\circ}\text{C}$) (电感负载) / (inductive load)	E_{off}		3.31 4.94 5.62		
短路数据 SC data	$V_{GE}\leq 15\text{V}, V_{CC}=800\text{V}$ $V_{CEmax}=V_{CES}-L_{sCE}\cdot di/dt$ $t_p\leq 10\text{us}, T_{vj}=150^{\circ}\text{C}$	I_{SC}		448		A
在开关状态下温度 Temperature under switching conditions		$T_{vj\ op}$	-40		150	$^{\circ}\text{C}$

二极管, 逆变器 / Diode, Inverter

最大额定值 / Maximum Ratings

Parameter	Conditions	Symbol	Value	Unit
反向重复峰值电压 Repetitive peak reverse voltage	$T_{vj}=25^{\circ}\text{C}$	V_{RRM}	1200	V
连续正向直流电流 Continuous DC forward current		I_F	100	A
正向重复峰值电流 Repetitive peak forward current	$t_p=1\text{ms}$	I_{FRM}	200	A
I^2t 值 I^2t -value	$t_p=10\text{ms}, \sin 180^{\circ}, T_{vj}=125^{\circ}\text{C}$	I^2t	1920	A^2s

特征值 / Characteristic Values

Parameter	Conditions	Symbol	Value			Unit
			Min.	Typ.	Max.	
正向电压 Forward voltage	I _F =100A, V _{GE} =0V	T _{vj} =25°C	V _F	2.38	2.60	V
	I _F =100A, V _{GE} =0V	T _{vj} =125°C			1.91	
	I _F =100A, V _{GE} =0V	T _{vj} =150°C			1.79	
反向恢复峰值电流 Peak reverse recovery current	I _F =100A,	T _{vj} =25°C	I _{RM}	57	92	A
	-dI _F /dt=1900A/μs(T _{vj} =150°C)	T _{vj} =125°C				
	V _R =600V, V _{GE} =-15V	T _{vj} =150°C			104	
恢复电荷 Recovered charge	I _F =100A,	T _{vj} =25°C	Q _r	4.28	10.83	μC
	-dI _F /dt=1900A/μs(T _{vj} =150°C)	T _{vj} =125°C				
	V _R =600V, V _{GE} =-15V	T _{vj} =150°C			13.21	
反向恢复损耗 (每脉冲) Reverse recovered energy	I _F =100A,	T _{vj} =25°C	E _{rec}	1.49	3.68	mJ
	-dI _F /dt=1900A/μs(T _{vj} =150°C)	T _{vj} =125°C				
	V _R =600V, V _{GE} =-15V	T _{vj} =150°C			4.51	
在开关状态下温度 Temperature under switching conditions		T _{vj op}	-40		150	°C

模块 / Module

Parameter	Conditions	Symbol	Value			Unit
绝缘测试电压 Isolation test voltage	RMS, f=50Hz, t=1min	V _{ISOL}	4000			V
内部绝缘 Internal isolation			Al ₂ O ₃			
储存温度 Storage temperature		T _{stg}	-40		125	°C
模块安装的扭矩 Mounting torque for modul mounting		M	3.0		5.0	Nm
端子连接扭矩 Terminal Connection Torque		M	2.5		5.0	Nm
重量 Weight		W		155		g

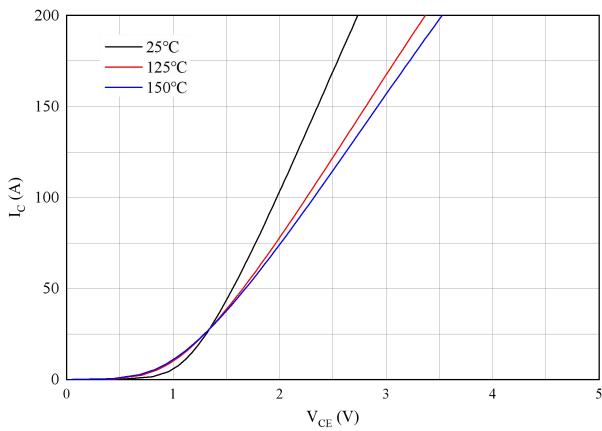
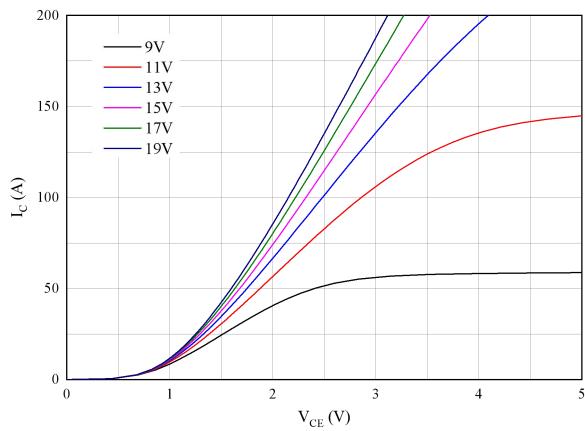
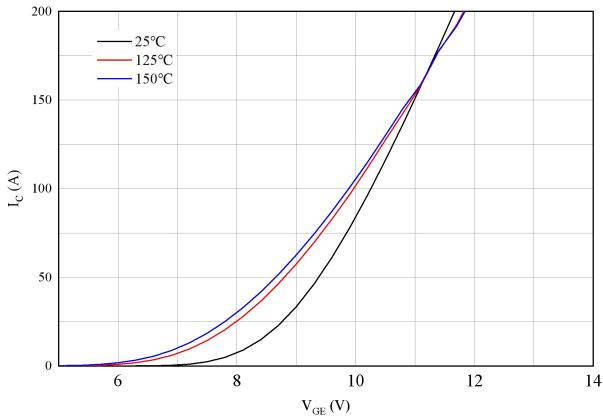
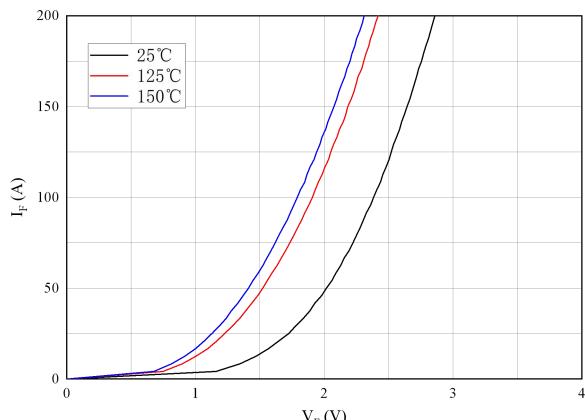
图 1. 典型输出特性 ($V_{GE}=15\text{V}$)Figure 1. Typical output characteristics ($V_{GE}=15\text{V}$)图 2. 典型输出特性 ($T_{vj}=150^\circ\text{C}$)Figure 2. Typical output characteristics ($T_{vj}=150^\circ\text{C}$)图 3. 典型传输特性($V_{CE}=20\text{V}$)Figure 3. Typical transfer characteristics ($V_{CE}=20\text{V}$)

图 4. 正向偏压特性 二极管

Figure 4. Forward characteristics of Diode

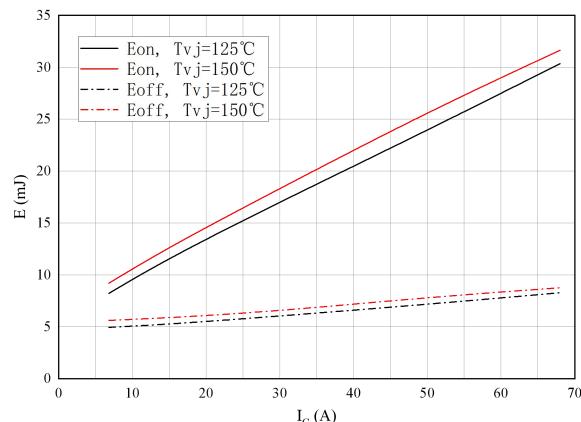


图 5. 开关损耗 逆变器

Figure 5. Switching losses of IGBT

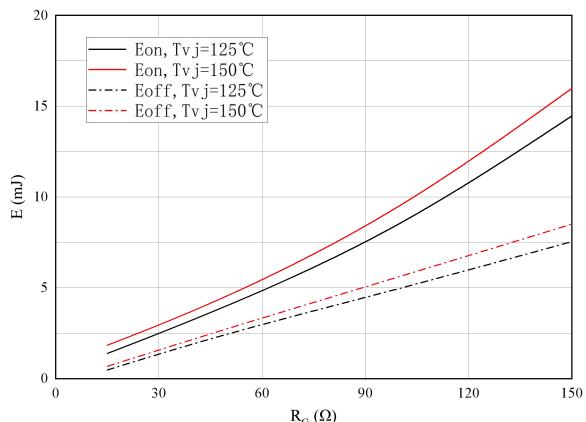
 $V_{GE}=\pm 15\text{V}$, $R_{Gon}=6.8\Omega$, $R_{Goff}=6.8\Omega$, $V_{CE}=600\text{V}$ 

图 6. 开关损耗 逆变器

Figure 6. Switching losses of IGBT

 $V_{GE}=\pm 15\text{V}$, $I_C=100\text{A}$, $V_{CE}=600\text{V}$

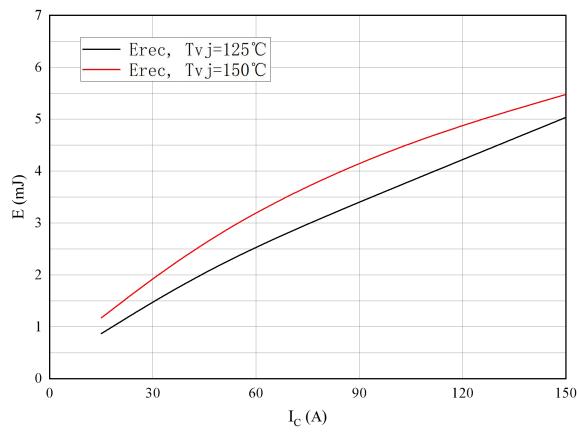


图 7. 开关损耗 二极管

Figure 7. Switching losses of Diode
RGon=6.8 Ω, VCE=600V

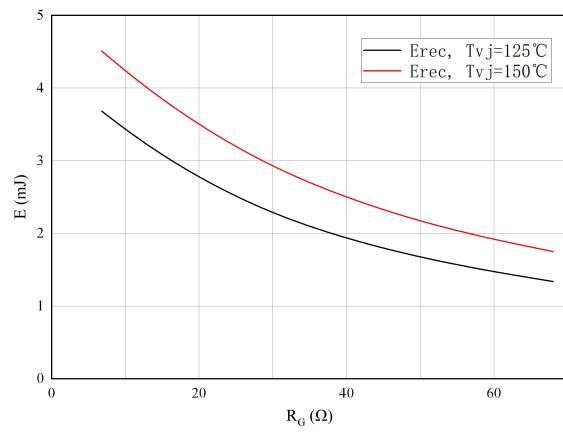


图 8. 开关损耗 二极管

Figure 8. Switching losses of Diode
IF=100A, VCE=600V

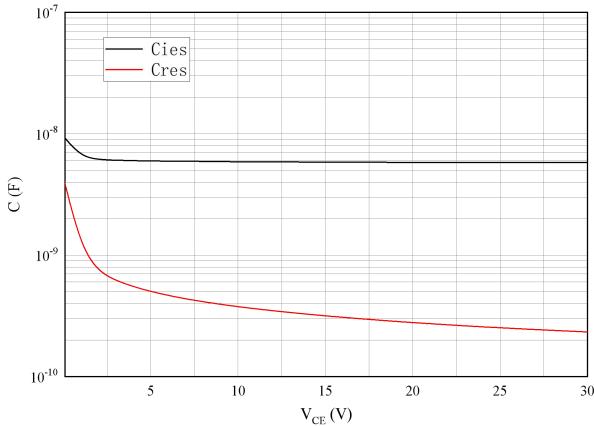
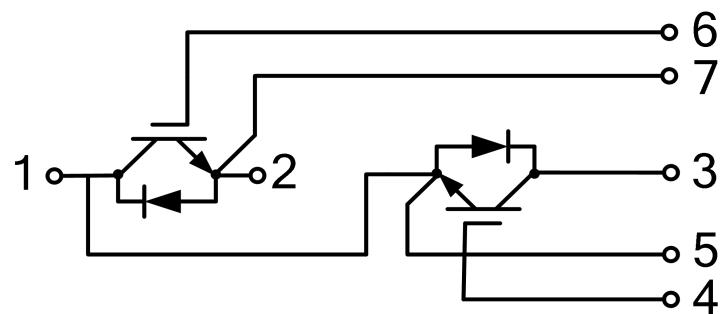


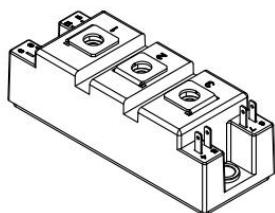
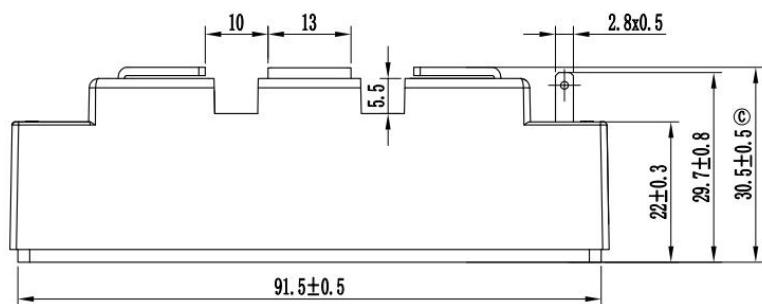
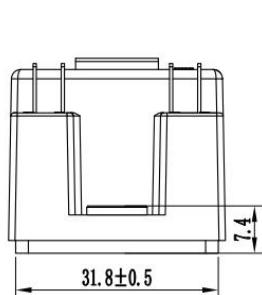
图 9. 电容特性

Figure 9. Capacitance characteristics

接线图 / Circuit diagram



封装尺寸 / Package outlines



注: 1. (C) 为重点尺寸标识
2. 未标注公差按GB/T1804-m执行

